

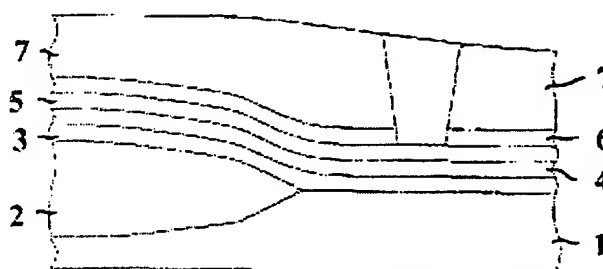
Lithographic process used in emitter structuring of bipolar transistors comprises forming photo-lacquer layer on antireflection layer on substrate and etching

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Abstract of DE19852852

The lithographic process comprises depositing an auxiliary layer (5) onto a silicon substrate (1) having a base layer (3) and emitter window layer (4), forming an organic antireflection layer (6) on the auxiliary layer, forming a photo-lacquer layer as a resist layer (7) on the antireflection layer, transferring the structures into the antireflection layer and then into the auxiliary layer by etching, removing the resist layer and antireflection layer and wet chemical etching the emitter window.



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